

INFORMATION DISCLOSURE  
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Tetsuya NITTA, et al.FILING DATE  
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GROUP

## U.S. PATENT DOCUMENTS

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## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number & Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
A-S-		JP 6-318561	11/15/1994	HAYASHI		abstract	
		JP 11-238806	08/31/1999	KITADE		abstract	
		JP 11-111855	04/23/1999	HIGUCHI		abstract	

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
A-S		LUDIKHUIZE, et al. "Extended (180V) Voltage in 0.8µm Thin-Layer-SOI A-BCD3 Technology on 1µm BOX for Display, Automotive & Consumer Applications" Proceedings of the 14th International Symposium on Power Semiconductor Devices & ICs, Santa Fe, NM (June 4-7, 2002) pp.77-80.	

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